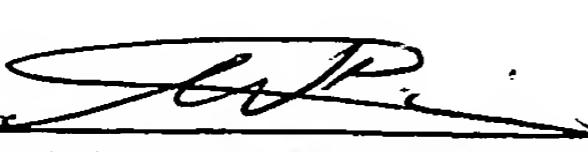


PTO-1449 Information Disclosure Citation in an Application			Application No. <i>Unassigned</i>	Applicant(s): STARIKOV ET AL.			
			Docket Number 065238.0128	Group Art Unit 2814	Filing Date 08/18/2003		
U.S. PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES <input type="checkbox"/> NO <input type="checkbox"/>
NON-PATENT DOCUMENTS							
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W54	O	TEMPEZ, ET AL., "PHOTOENHANCED REACTIVE ION ETCHING OF III-V NITRIDES IN BCl ₃ /Cl ₂ /AR/N ₂ PLASMAS," <i>J. VAC. SCI. TECHNOL. A 17(4)</i> , JUL/AUG 1999, PG. 2209-2213				1999	
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EXAMINER 				DATE CONSIDERED <i>12/18/04</i>			
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							